PD - 91737A

International
IOR Rectifier

RADIATION HARDENED POWER MOSFET SURFACE MOUNT(SMD-3)

IRHNB7064

60V, N-CHANNEL

RAD Hard™ HEXFET® TECHNOLOGY

Product Summary

Part Number	Radiation Level	$R_{DS(on)}$	I_D
IRHNA7064	100K Rads (Si)	0.015Ω	75*A
IRHNA3064	300K Rads (Si)	0.015Ω	75*A
IRHNA4064	600K Rads (Si)	0.015Ω	75*A
IRHNA8064	1000K Rads (Si)	0.015Ω	75*A

SMD-3

International Rectifier's RADHard HEXFET® technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low Rdson and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Low $R_{DS(on)}$
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Surface Mount
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I_D @ V_{GS} = 12V, T_C = 25°C	Continuous Drain Current	75*	A
I_D @ V_{GS} = 12V, T_C = 100°C	Continuous Drain Current	56	
I_{DM}	Pulsed Drain Current ①	300	
P_D @ T_C = 25°C	Max. Power Dissipation	300	W
	Linear Derating Factor	2.4	W/°C
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulse Avalanche Energy ②	500	mJ
I_{AR}	Avalanche Current ①	75*	A
E_{AR}	Repetitive Avalanche Energy ①	30	mJ
dv/dt	Peak Diode Recovery dv/dt ③	2.5	V/ns
T_J T_{STG}	Operating Junction Storage Temperature Range	-55 to 150	°C
	Package Mounting Surface Temperature	300 (for 5 sec.)	
	Weight	3.5 (Typical)	g

For footnotes refer to the last page
*Current is limited by pin diameter

Electrical Characteristics @ Tj = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V_{GS} = 0V, I_D = 1.0mA
$\Delta BV_{DSS}/\Delta T_J$	Temperature Coefficient of Breakdown Voltage	—	0.056	—	V/°C	Reference to 25°C, I_D = 1.0mA
$R_{DS(on)}$	Static Drain-to-Source On-State Resistance	—	—	0.015	Ω	V_{GS} = 12V, I_D = 56A ④
		—	—	0.018		V_{GS} = 12V, I_D = 75A
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	V_{DS} = V_{GS}, I_D = 1.0mA
g_{fs}	Forward Transconductance	18	—	—	S (℧)	V_{DS} > 15V, I_{DS} = 56A ④
I_{DSS}	Zero Gate Voltage Drain Current	—	—	25	μA	V_{DS}= 48V ,V_{GS}=0V
		—	—	250		V_{DS} = 48V, V_{GS} = 0V, T_J = 125°C
I_{GSS}	Gate-to-Source Leakage Forward	—	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	—	-100		V_{GS} = -20V
Q_g	Total Gate Charge	—	—	260	nC	V_{GS} =12V, I_D = 75A V_{DS} = 30V
Q_{gs}	Gate-to-Source Charge	—	—	60		
Q_{gd}	Gate-to-Drain (‘Miller’) Charge	—	—	86		
$t_{d(on)}$	Turn-On Delay Time	—	—	27	ns	V_{DD} =30V, I_D = 75A V_{GS} =12V, R_G = 2.35Ω
t_r	Rise Time	—	—	120		
$t_{d(off)}$	Turn-Off Delay Time	—	—	76		
t_f	Fall Time	—	—	93		
$L_S + L_D$	Total Inductance	—	4.0	—	nH	Measured from the center of drain pad to center of source pad
C_{iss}	Input Capacitance	—	4900	—	pF	V_{GS} = 0V, V_{DS} = 25V f = 1.0MHz
C_{oss}	Output Capacitance	—	2800	—		
C_{rss}	Reverse Transfer Capacitance	—	860	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I_S	Continuous Source Current (Body Diode)	—	—	75*	A	
I_{SM}	Pulse Source Current (Body Diode) ①	—	—	356		
V_{SD}	Diode Forward Voltage	—	—	3.0	V	T_j = 25°C, I_S = 75A, V_{GS} = 0V ④
t_{rr}	Reverse Recovery Time	—	—	220	nS	T_j = 25°C, I_F = 75A, di/dt ≤ 100A/μs V_{DD} ≤ 50V ④
Q_{RR}	Reverse Recovery Charge	—	—	3.1	μC	
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L_S + L_D.				

*Current is limited by the internal wire diameter

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R_{thJC}	Junction-to-Case	—	—	0.42	°C/W	
$R_{thJ\text{-}PCB}$	Junction-to-PC board	—	1.6	—		Soldered to a 1” sq. copper-clad board

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

Radiation Characteristics

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100 K Rads (Si)[1]		300-1000K Rads (Si)[2]		Units	Test Conditions
		Min	Max	Min	Max		
BV_{DSS}	Drain-to-Source Breakdown Voltage	60	—	60	—	V	V_{GS} = 12V, I_D = 1.0mA
$V_{GS(th)}$	Gate Threshold Voltage	2.0	4.0	1.25	4.5		$V_{GS} = V_{DS}$, I_D = 1.0mA
I_{GSS}	Gate-to-Source Leakage Forward	—	100	—	100	nA	V_{GS} = 20V
I_{GSS}	Gate-to-Source Leakage Reverse	—	-100	—	-100		V_{GS} = -20 V
I_{DSS}	Zero Gate Voltage Drain Current	—	25	—	50	µA	V_{DS}=48V, V_{GS} =0V
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.015	—	0.025	Ω	V_{GS} = 12V, I_D =56A
$R_{DS(on)}$	Static Drain-to-Source ④ On-State Resistance (SMD-3)	—	0.015	—	0.025	Ω	V_{GS} = 12V, I_D =56A
V_{SD}	Diode Forward Voltage ④	—	3.0	—	3.0	V	V_{GS} = 0V, I_S = 75A

1. Part number IRHNB7064
2. Part numbers IRHNB8064, RHNB3064, and IRHNB4064

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm²))	Energy (MeV)	Range (µm)	VDS(V)				
				@VGS=0V	@VGS=-5V	@VGS=-10V	@VGS=-15V	@VGS=-20V
I	59.9	345	32.8	60	60	45	40	30
Br	36.8	305	39	40	35	30	25	20

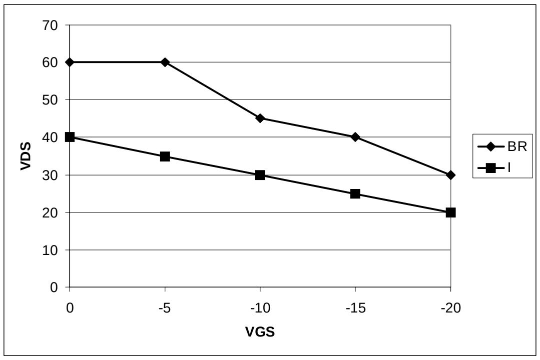


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

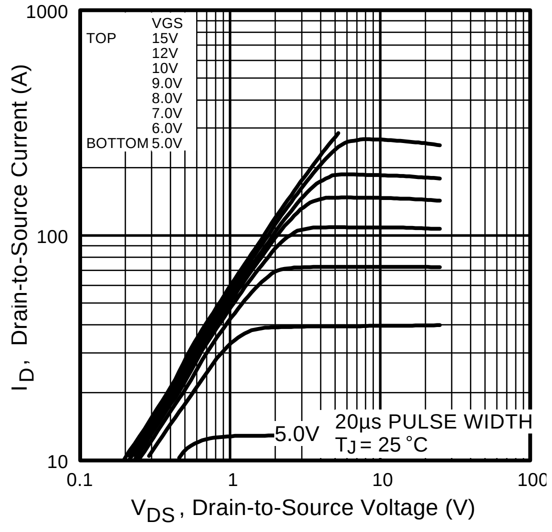


Fig 1. Typical Output Characteristics

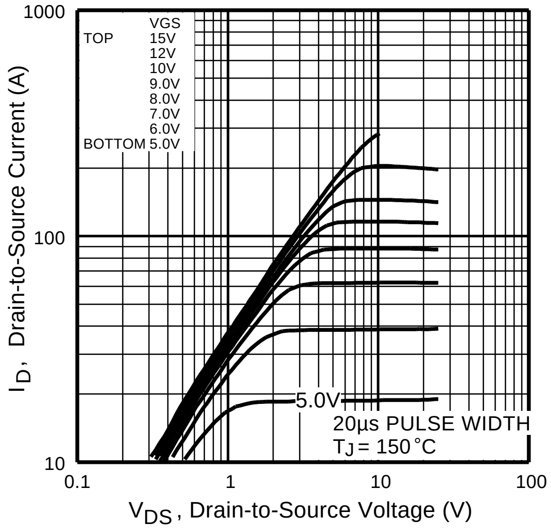


Fig 2. Typical Output Characteristics

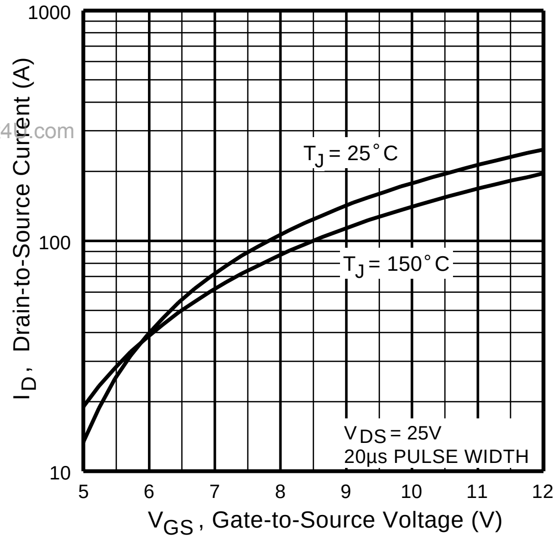


Fig 3. Typical Transfer Characteristics

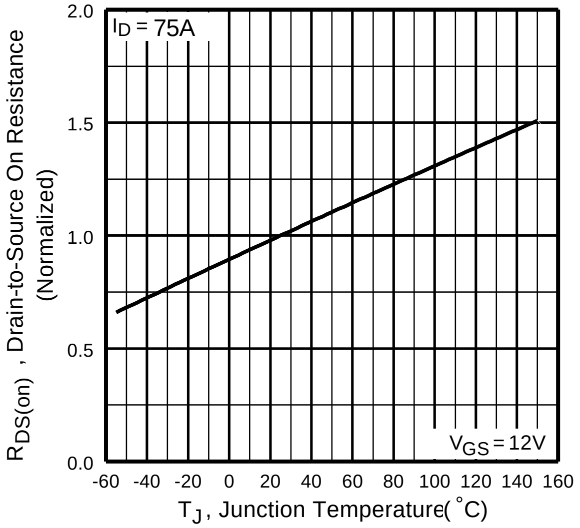


Fig 4. Normalized On-Resistance
Vs. Temperature

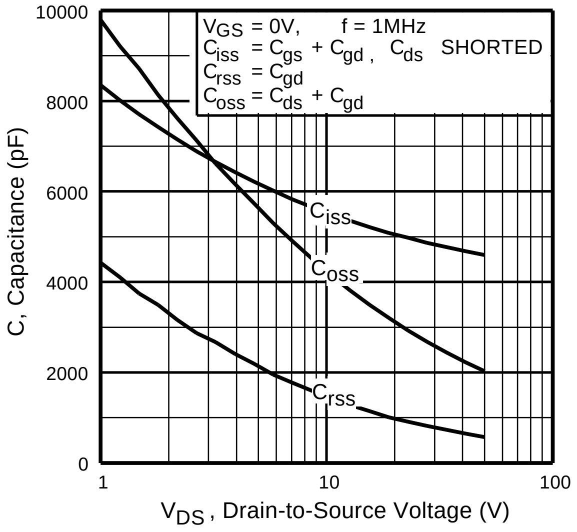


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

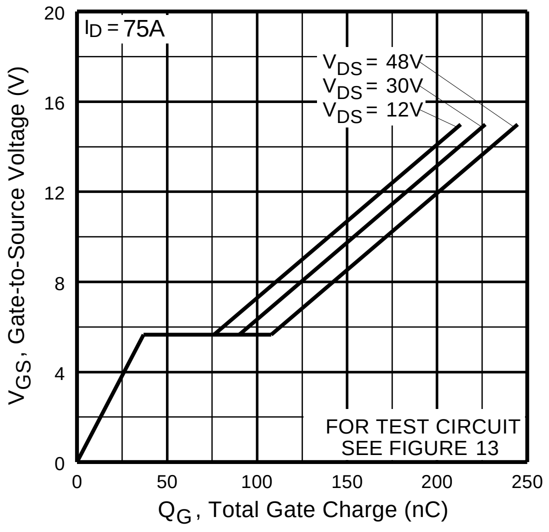


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

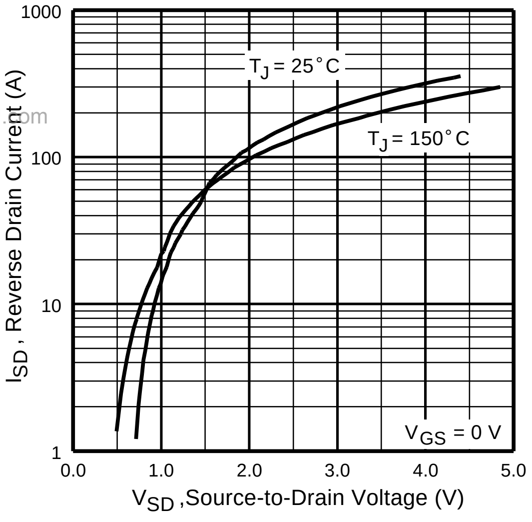


Fig 7. Typical Source-Drain Diode Forward Voltage

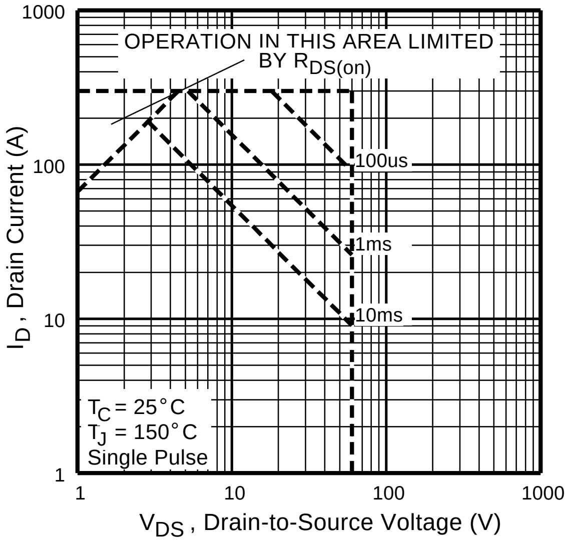


Fig 8. Maximum Safe Operating Area

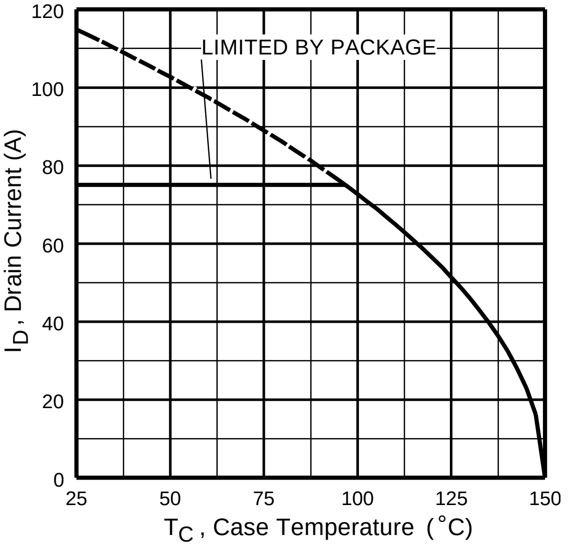


Fig 9. Maximum Drain Current Vs. Case Temperature

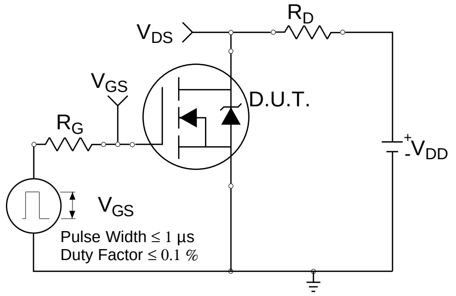


Fig 10a. Switching Time Test Circuit

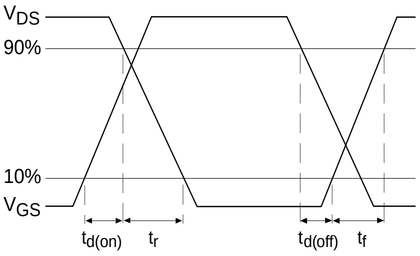


Fig 10b. Switching Time Waveforms

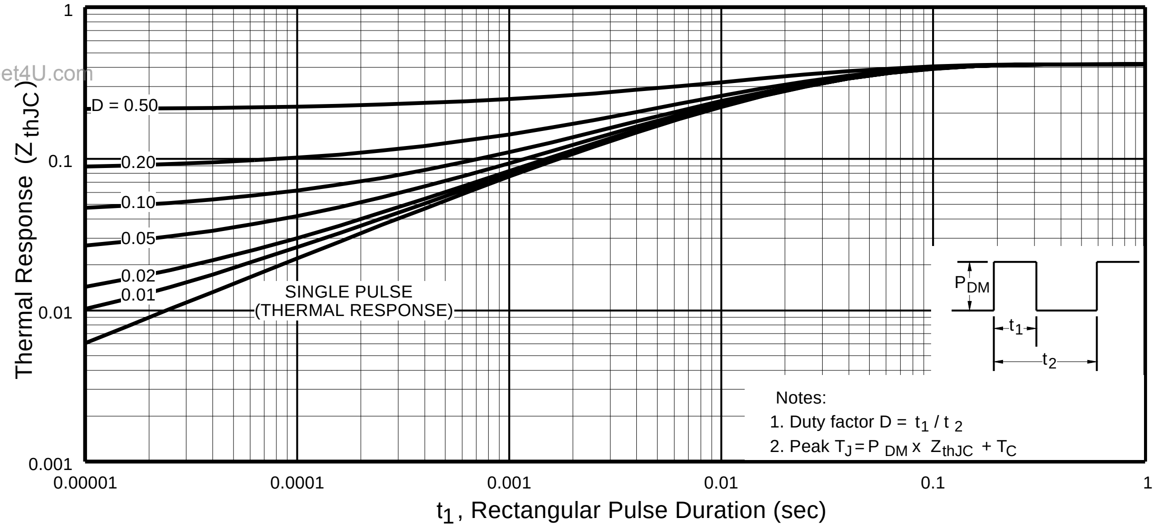


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

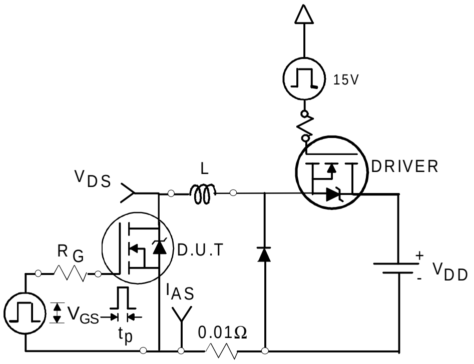


Fig 12a. Unclamped Inductive Test Circuit

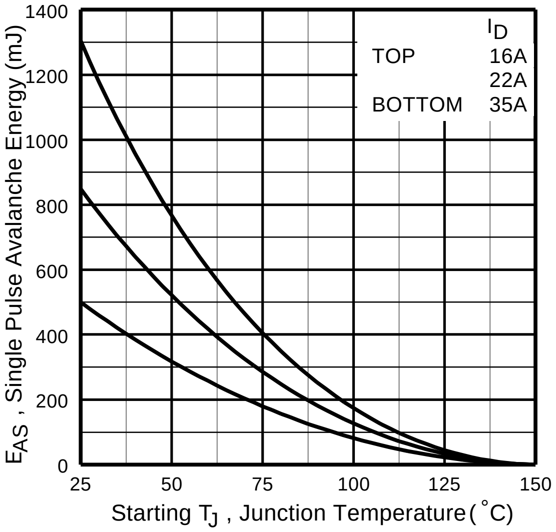


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

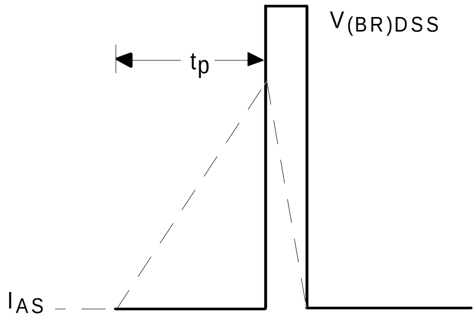
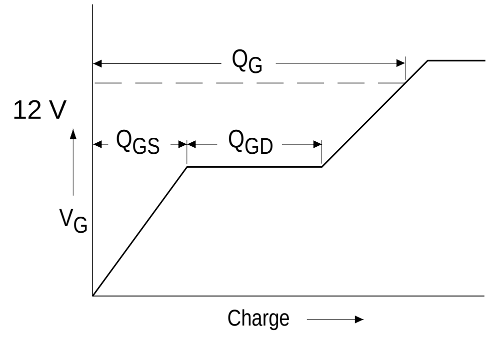


Fig 12b. Unclamped Inductive Waveforms



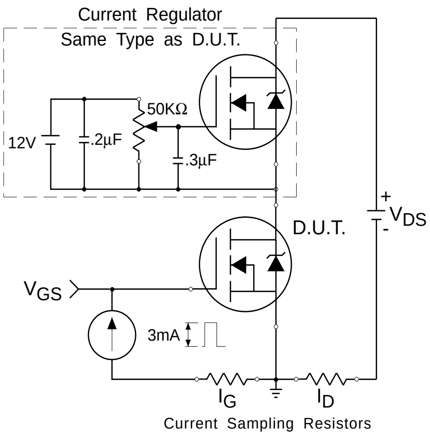


Fig 13a. Basic Gate Charge Waveform

Fig 13b. Gate Charge Test Circuit

Foot Notes:

① Repetitive Rating; Pulse width limited by maximum junction temperature.

② V_{DD} = 25V, starting T_J = 25°C, L=0.17mH
Peak I_L = 75A, V_{GS} =12V

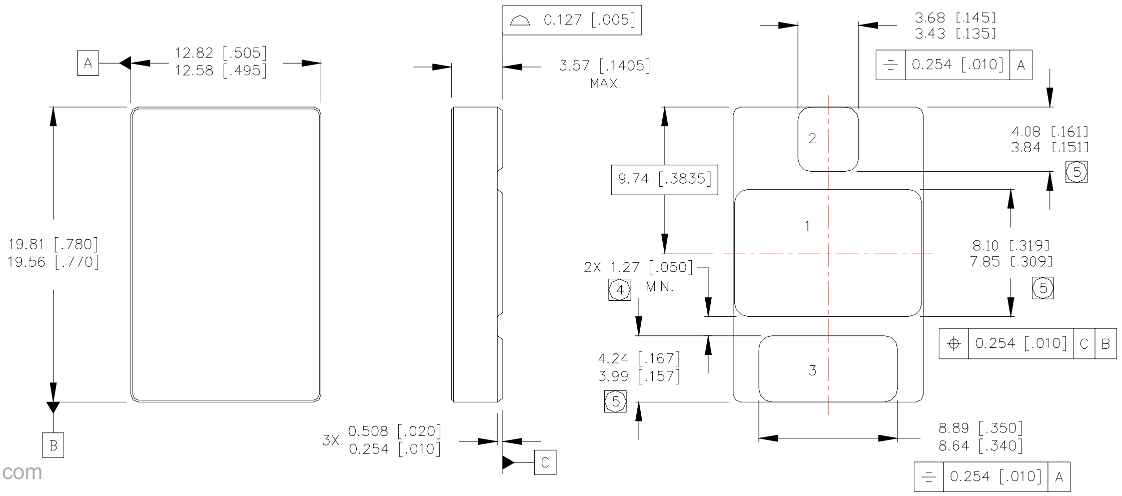
③ $I_{SD} \leq$ 75A, di/dt $\leq$ 220A/µs,
$V_{DD} \leq$ 60V, $T_J \leq$ 150°C

④ Pulse width $\leq$ 300 µs; Duty Cycle $\leq$ 2%

⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and V_{DS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

⑥ **Total Dose Irradiation with V_{DS} Bias.**
48 volt V_{DS} applied and V_{GS} = 0 during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — SMD-3



NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M–1994.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

④ DIMENSION INCLUDES METALLIZATION FLASH.
⑤ DIMENSION DOES NOT INCLUDE METALLIZATION FLASH.

PAD ASSIGNMENTS

1 = DRAIN
2 = GATE
3 = SOURCE

International
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